

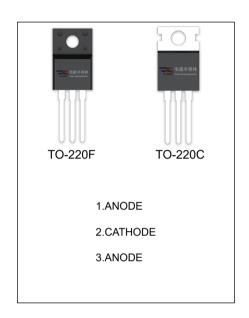
# SBD30120TCTB SBDF30120TCTB SCHOTTKY BARRIER RECTIFIER

#### MAIN CHARACTERISTICS

Io	30 (2×15) A
$V_{RRM}$	120 V
T <sub>j</sub>	150 ℃
$V_{F(typ)}$	0.68V (@Tj=125℃)

### **FEATURES**

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



# MAXIMUM RATINGS ( T<sub>a</sub>=25℃ unless otherwise noted )

Cymphal	Parameter	SBD		Hoit	
Symbol	Parameter		F30120TCTB	Unit	
$V_{RRM}$	Peak repetitive reverse voltage	120		V	
$V_{RWM}$	Working peak reverse voltage				
$V_R$	DC blocking voltage				
V <sub>R(RMS)</sub>	RMS reverse voltage	84		V	
lo	Average rectified output current	30		Α	
I <sub>FSM</sub>	Non-Repetitive peak forward surge current (8.3ms half sine wave)	200		Α	
R <sub>⊝Jc</sub>	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W	
R <sub>OJA</sub>	Thermal resistance from junction to ambient	62.5		°C/W	
Tj	Junction temperature	150		$^{\circ}$	
T <sub>stg</sub>	Storage temperature	-55~+150		$^{\circ}$	

## ELECTRICAL CHARACTERISTICS (T₂=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		 Тур	Max	Unit V
Reverse voltage	V <sub>(BR)</sub>					
Reverse current	I <sub>R</sub>	V <sub>R</sub> =120V	Tj =25℃	10	100	uA
			Tj =125℃	10		mA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =10A	Tj =25℃	0.69		V
			Tj =125℃	0.61		V
		I <sub>F</sub> =15A	Tj =25℃	0.83	0.89	V
			Tj =125℃	0.68		V

<sup>\*</sup>Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



